

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	1561	((In with Ga with N) or (indium near2 gallium near2 nitride)) and (nitride near2 semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/31 08:01
L7	1561	((("In" with "Ga" with "N") or (indium near2 gallium near2 nitride)) and (nitride near2 semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/31 08:01
L9	156	(nitride near2 semiconductor) and clad\$3 and active and substrate and (conductivity or guide or buffer) and ((In with Ga with N) or (indium near2 gallium near2 nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:02
L6	113	(nitride near2 semiconductor) and clad\$3 and active and substrate and (conductivity or guide or buffer) and (In with Ga with N)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:02
L10	87	(nitride near2 semiconductor) and clad\$3 and active and substrate and (conductivity or guide or buffer) and ((In with Ga with N) or (indium near2 gallium near2 nitride))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:11
L5	6	In"y"GaN"1-y"N with (buffer or conductivity or guide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/31 08:11
L12	36	(nitride near2 semiconductor) and clad\$3 and active and substrate and ((conductivity or guide or buffer) near2 (layer or region or medium or film)) and ((In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N) or (indium near2 gallium near2 nitride))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:13
L15	2	(nitride near2 semiconductor) and clad\$3 and active and substrate and ((conductivity or guide or buffer) near2 (layer or region or medium or film)) and (In"y" near2 Ga"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N)	US-PGPUB	AND	ON	2005/10/31 08:19
L14	19	(nitride near2 semiconductor) and clad\$3 and active and substrate and ((conductivity or guide or buffer) near2 (layer or region or medium or film)) and ((In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N) or (indium near2 gallium near2 nitride))	US-PGPUB	AND	ON	2005/10/31 08:19
L16	2	(nitride near2 semiconductor) and clad\$3 and active and substrate and ((conductivity or guide or buffer) near2 (layer or region or medium or film)) and (In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N)	US-PGPUB	AND	ON	2005/10/31 08:21
L18	10	(nitride near2 semiconductor) and clad\$3 and active and substrate and (In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:29
L17	6	(nitride near2 semiconductor) and clad\$3 and active and substrate and ((conductivity or guide or buffer) near2 (layer or region or medium or film)) and (In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:29
L19	18	clad\$3 and active and substrate and (In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 08:33
L20	26	clad\$3 and active and substrate and (In"y"GaN"1-y"N or In"x"GaN"1-x"N or In"z"GaN"1-z"N or (In near2 "y" near2 Ga near2 "1-y" near2 N) or (In near2 "x" near2 Ga near2 "1-x" near2 N) or (In near2 "z" near2 Ga near2 "1-z" near2 N))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 09:54

L23	0	("JP11008437").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/31 10:20
L22	61	21 not 20	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 10:20
L25	198	((("4761791") or ("4779282") or ("4875217") or ("5309471") or ("5583878") or ("5707892") or ("4365336") or ("4392228") or ("4456999") or ("4532631") or ("4792959") or ("5214662") or ("5253264") or ("5295150") or ("5336635") or ("5375136") or ("5394421") or ("5580818") or ("5621837") or ("5642372") or ("5675605") or ("5684307") or ("5757985") or ("5790580") or ("5832019") or ("5834329") or ("5847415") or ("5913107") or ("5917846") or ("5932004") or ("6009113") or ("6027254") or ("6164836") or ("4296387") or ("4315226") or ("4329660") or ("4329661") or ("4333061") or ("4339689") or ("4358850") or ("4360919") or ("4360920") or ("4366568") or ("4369513") or ("4371967") or ("4377865") or ("4380861") or ("4383319") or ("4392227") or ("4408330").pn.) or ("4425650") or ("4426700") or ("4429397") or ("4432092") or ("4456998") or ("4488306") or ("4488304") or ("4506366") or ("4520485") or ("4599787") or ("4607369") or ("4607368") or ("4622627") or ("4630083") or ("4755015") or ("4757509") or ("4758532") or ("4758535") or ("4768200") or ("4769342") or ("4769821") or ("4779281") or ("4779283") or ("4794606") or ("4810670") or ("4813050") or ("4829534") or ("4835783") or ("4843031") or ("4847844") or ("4858241") or ("4862474") or ("4918496") or ("4928285") or ("4932033") or ("4946802") or ("4969151") or ("4972238") or ("4974233") or ("4978184") or ("4984243") or ("4990972") or ("4992837") or ("4994143") or ("5003359") or ("5010376") or ("5014096") or ("5016252") or ("5018159") or ("5019787").pn.)).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/31 10:31
L24	2	("11008437").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/31 10:31
L27	0	clad\$3 and active and substrate and ((ln"y"Ga"1-y"N or ln"x"Ga"1-x"N or ln"z"Ga"1-z"N or (ln near2 "y" near2 Ga near2 "1-y" near2 N) or (ln near2 "x" near2 Ga near2 "1-x" near2 N) or (ln near2 "z" near2 Ga near2 "1-z" near2 N)) or (indium near2 gallium near2 (nitride or nitrogen))) and 25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 10:38
L26	122	clad\$3 and active and substrate and ((ln"y"Ga"1-y"N or ln"x"Ga"1-x"N or ln"z"Ga"1-z"N or (ln near2 "y" near2 Ga near2 "1-y" near2 N) or (ln near2 "x" near2 Ga near2 "1-x" near2 N) or (ln near2 "z" near2 Ga near2 "1-z" near2 N)) or (indium near2 gallium near2 (nitride or nitrogen)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 10:38
L21	87	clad\$3 and active and substrate and ((ln"y"Ga"1-y"N or ln"x"Ga"1-x"N or ln"z"Ga"1-z"N or (ln near2 "y" near2 Ga near2 "1-y" near2 N) or (ln near2 "x" near2 Ga near2 "1-x" near2 N) or (ln near2 "z" near2 Ga near2 "1-z" near2 N)) or (indium near2 gallium near2 (nitride or nitrogen)))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/31 10:38



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#2 ((nitride semiconductor and substrate and (clad or cladding) and (in~y~ga~1~y~n or in~x~ga~1~x~n or in~z~ga~1~z~n or (in near2 ~y~ near2 ga near2 ~1~y~ near2 n) or (in near2 ~x~ near2 ga near2 ~1~x~ near2 n) or (in near2 ~z~ near2 ga near2 ~1~z~ near2 n)) <in>metadata)

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#3 nitride semiconductor and (clad or cladding) and substrate and indium gallium Nitrogen

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